



Cadence Virtuoso LAB (6) Report

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Analog Electronics Workshop

DIFFERENTIAL AMPLIFIER

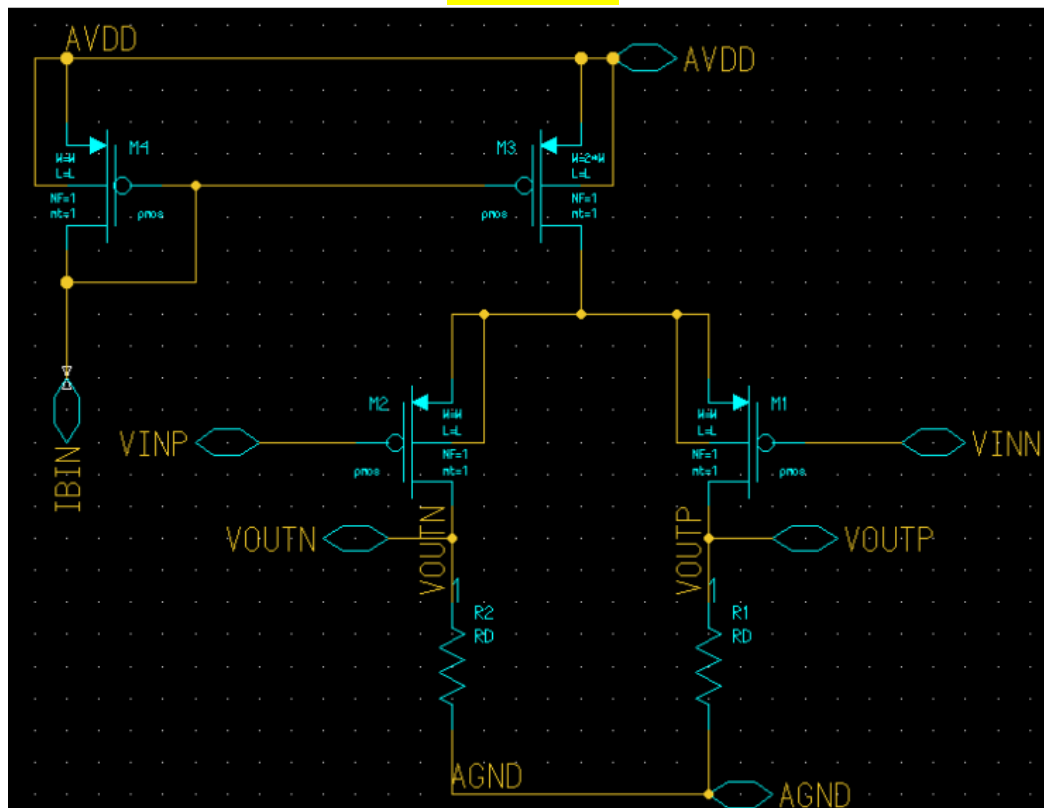
Part 1

SIZING CHART

Specs (Specifications)

For Each Transistor (I_D)	20 μ A.
Supply (V_{DD})	1.8 V.
Bias Current (I_{SS})	40 μ A.
Length (L)	1 μ m.
CM Output Level	0.7
Differential Gain	8
Width (W)	22.5 μ m.
g_m	229.5 μ S.
g_{ds}	1.644 μ S.

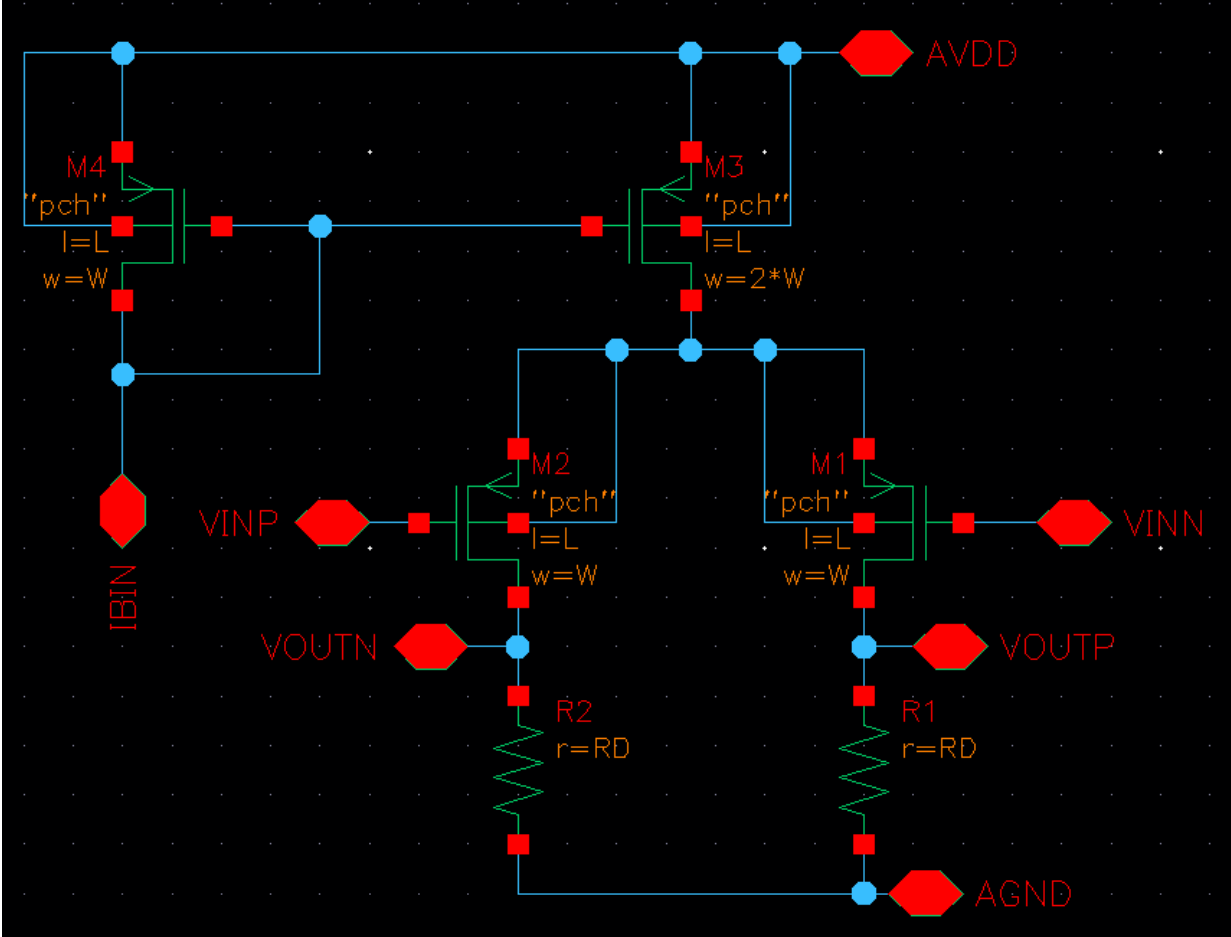
Circuit



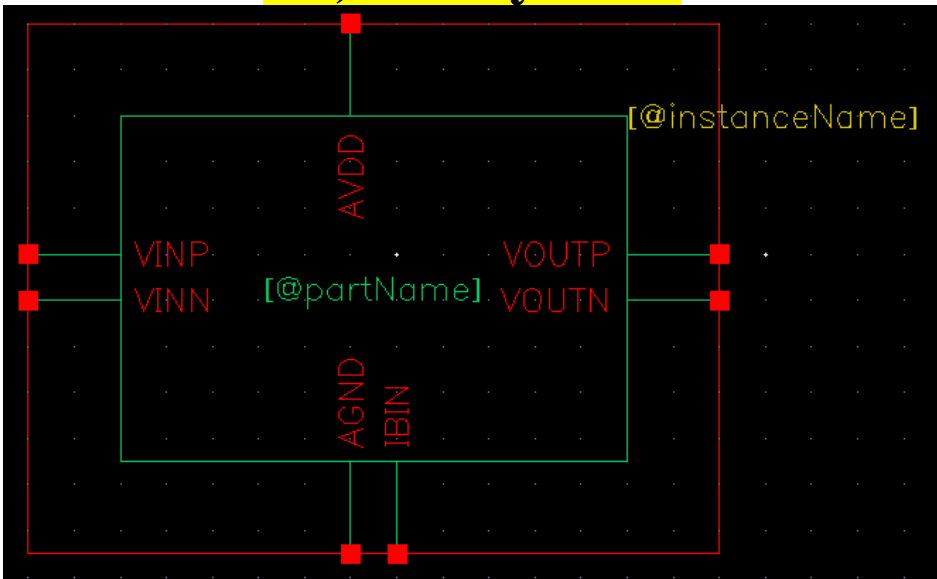
Part 2

DIFF AMPLIFIER

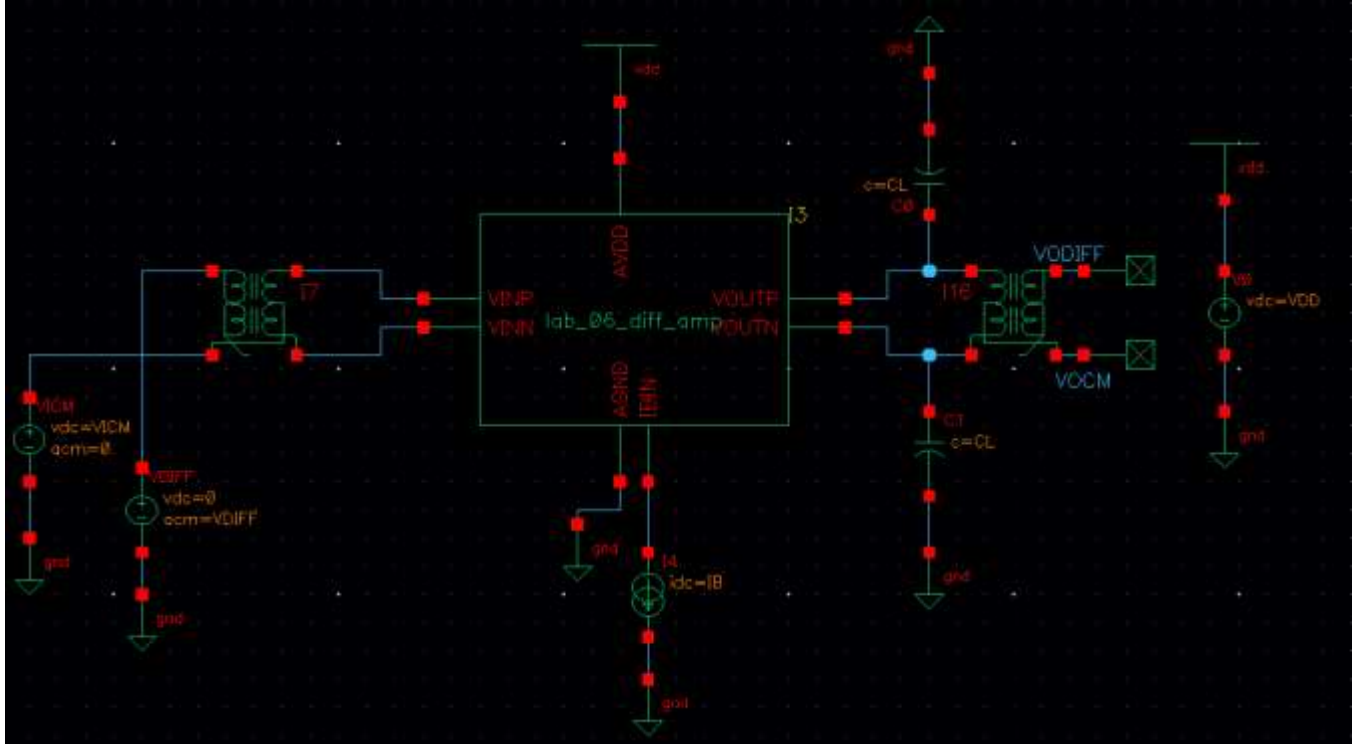
P1: Schematic



P2, P3: Symbol



P4, P5: Schematic



P6, P7, P8: Specs

Global Variables	
<input checked="" type="checkbox"/> CL	1p
<input checked="" type="checkbox"/> IB	20u
<input checked="" type="checkbox"/> L	1u
<input checked="" type="checkbox"/> RD	35k
<input checked="" type="checkbox"/> VDD	1.8
<input checked="" type="checkbox"/> VDIFF	0
<input checked="" type="checkbox"/> VICM	0.7
<input checked="" type="checkbox"/> W	22.5u

P9

✚ Analytically calculate the valid range for Vicm: the common mode input range (CMIR). Set Vicm at the center of this range.

→ To Make M_1 & M_2 In Saturation

$$V_g = VICM > V_D - |V_{th}|, R_D = \frac{V_{out}^{CM}}{I_D} = \frac{0.7 V}{20 \mu A} = 35 k\Omega$$

Since, $V_D = 0.7 V$, $V_{th} = 0.41 V$.

$$VICM \geq -|V_{th}| + \frac{1}{2} I_{SS} R_D$$

$$VICM_{Min} = V_D - V_{th} = 0.29 V.$$

→ To Make M_3 In Saturation

$$V_{DD} = V_{ov3} + V_{sg1} + VICM_{Max}$$

$$VICM_{Max} = V_{DD} - V_{ov3} - (V_{ov1} + |V_{th}|)$$

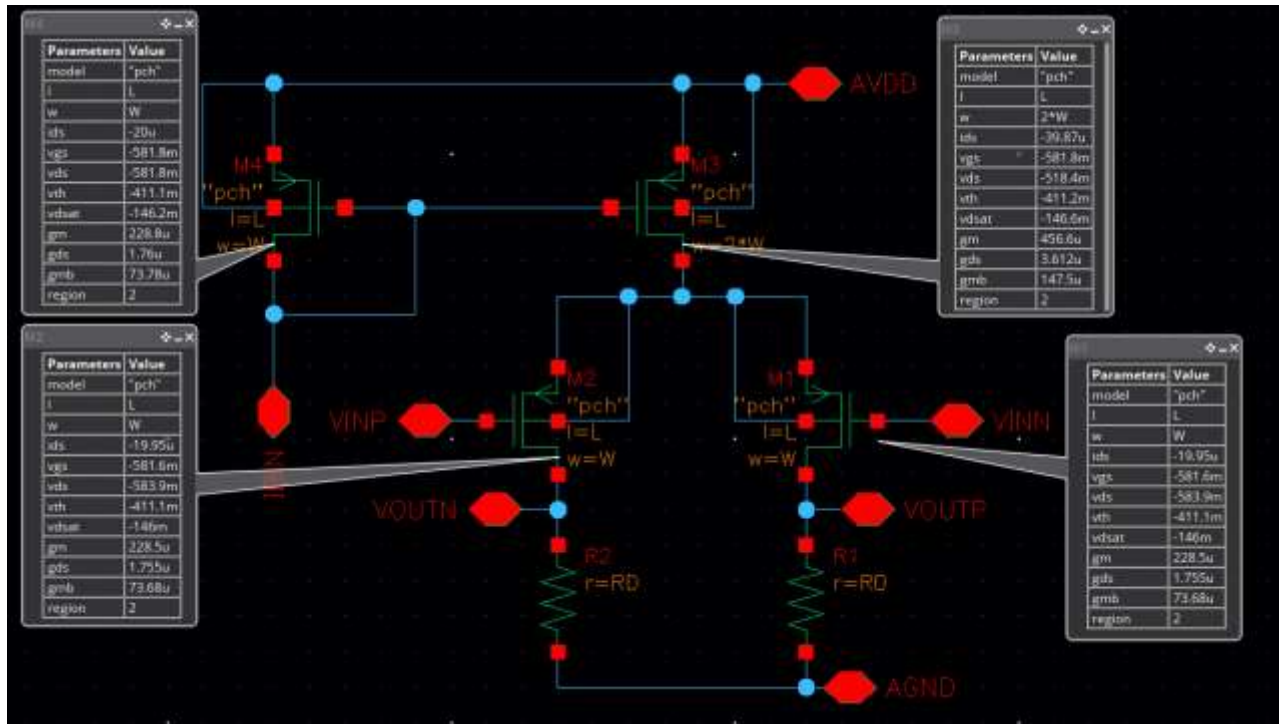
Since, $V_{ov3} = V_{ov1} = 170.5 mV$, $V_{th} = 0.41 V$.

$$VICM_{Max} = V_{DD} - 2V_{ov} - |V_{th}| = 1.049 V.$$

Report The Following: -

(1) OP Simulation

Report the schematic of the diff pair with DC OP point clearly annotated: I_d , V_{gs} , V_{ds} , V_{th} , V_{dsat} , g_m , g_{ds} , g_{mb} , region.



Q1

For M ₁ & M ₂		Parameters	For M ₃	For M ₄
I_{ds}	-19.95 μ A	I_{ds}	-39.87 μ A	20 μ A
V_{gs}	-581.6 mV	V_{gs}	-581.8 mV	-581.8 mV
V_{ds}	-583.9 mV	V_{ds}	-518.4 mV	-581.8 mV
V_{th}	-411.1 mV	V_{th}	-411.2 mV	-411.1 mV
V_{dsat}	-146 mV	V_{dsat}	-146.6 mV	-146.2 mV
g_m	228.5 μ S	g_m	456.6 μ S	228.8 μ S
g_{ds}	1.755 μ S	g_{ds}	3.612 μ S	1.76 μ S
g_{mb}	73.68 μ S	g_{mb}	147.5 μ S	73.78 μ S
region	2	region	2	2

Q2

✚ Check that all transistors operate in saturation.

- From Above All Transistors have Region = 2 (In Saturation Region).

(2) Diff. Small Signal CCS.

Q1, Q2, Q3

Analyses

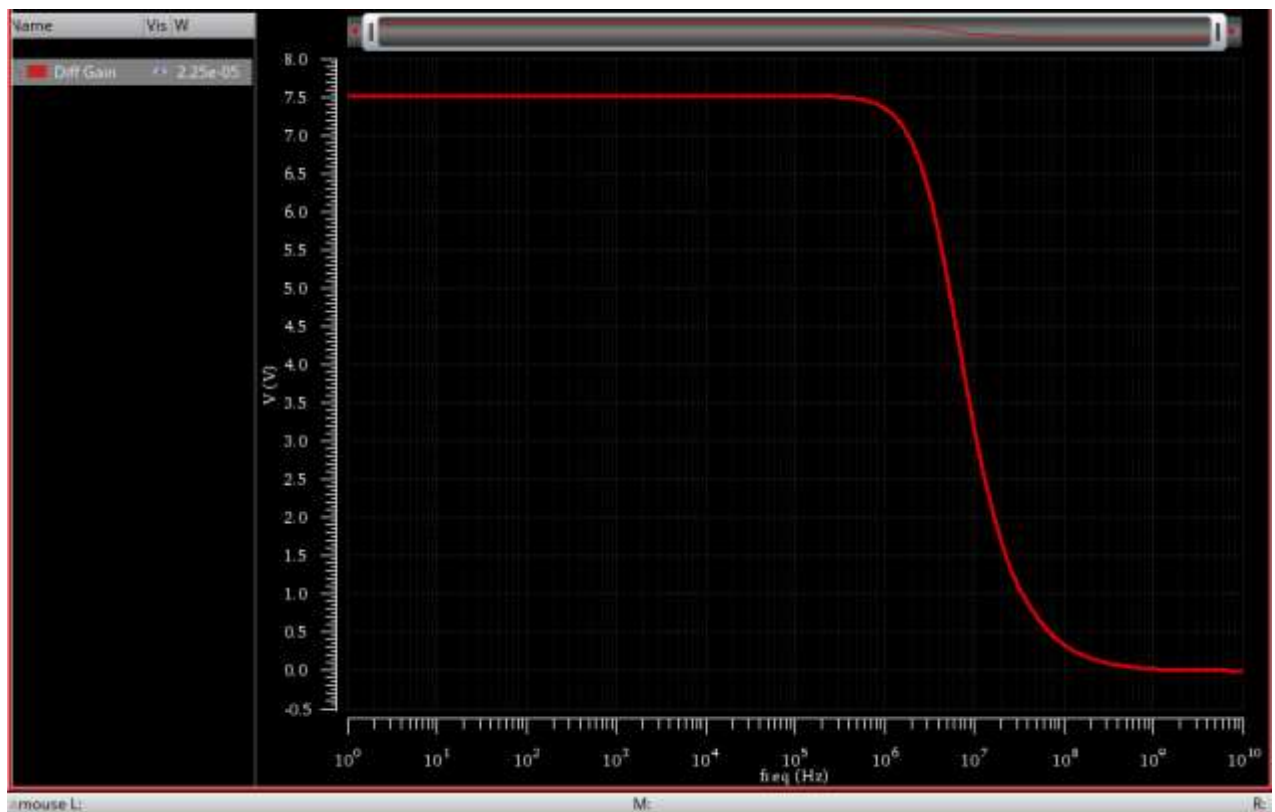
- ☒ ac 1 10G 10 Logarithmic Points Per Decade Start-Stop
- ☐ dc t

Global Variables

- ☒ CL 1p
- ☒ IB 20u
- ☒ L 1u
- ☒ RD 35k
- ☒ VDD 1.8
- ☒ VDIFF 1
- ☒ VICM 0.7
- ☒ W 22.5u

Report the Bode plot of small signal diff gain.

Q4



Q5

Compare the DC diff gain and BW with hand analysis in a table.

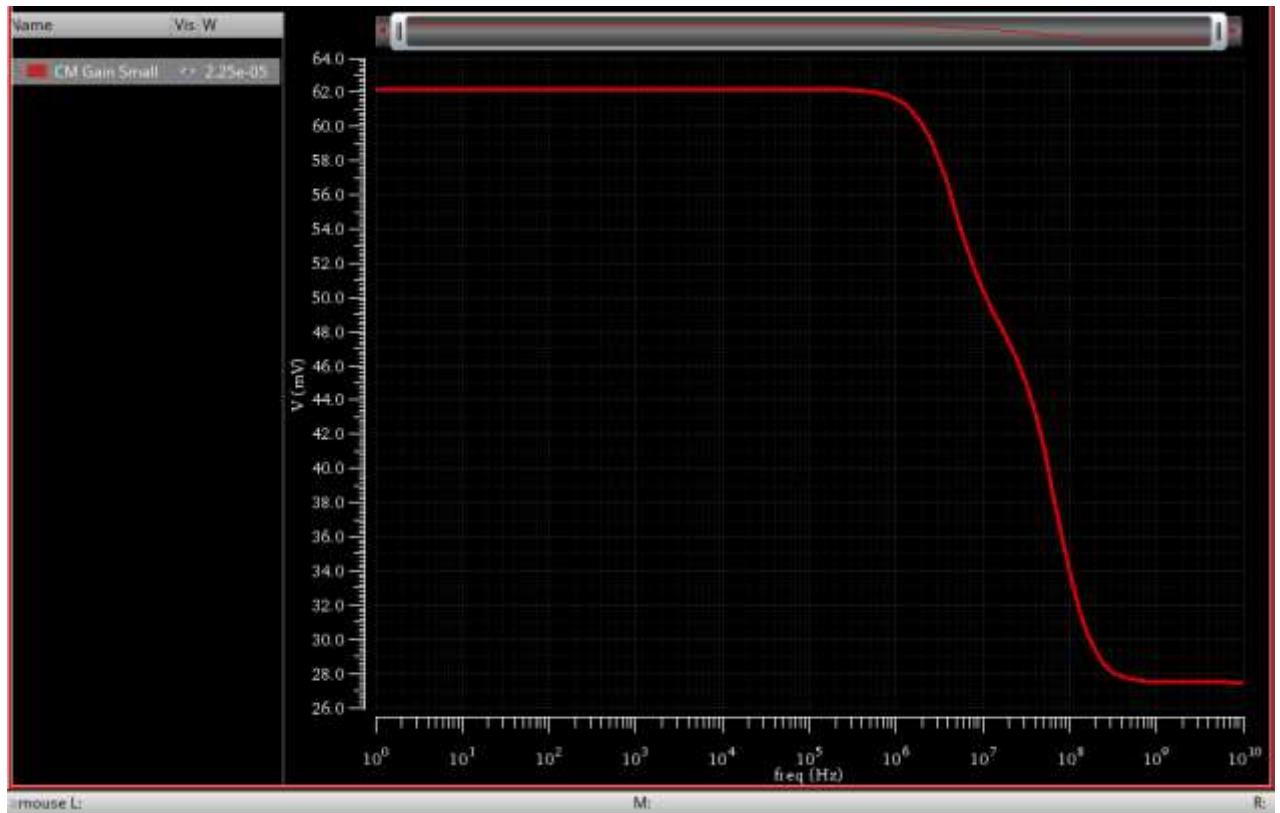
P.O.C	Simulation	Hand Analysis
Diff Gain (A_{Diff})	7.53	$A_V = g_m * (R_D // r_o)$
BW	4.678 MHZ	$BW = \frac{1}{2\pi R_D C_L} = 4.54 \text{ MHZ}$

(3) CM Small Signal CCS.

Q1 Report the Bode plot of small signal CM gain.

Q2

Q3



Q4 Compare the DC CM gain with hand analysis in a table.
Is it smaller than “1”? Why?

POC	Simulation	Hand Analysis
CM Gain (A_{CM})	61 mV/V	$A_{CM} = \frac{g_m R_D}{1 + 2g_m r_{o3}} = 63 \text{ mV/V}$

Yes, it is Smaller than 1 Because R_{SS} is R_{LFD} Which Has too large Value to make the Current Source Ideal.

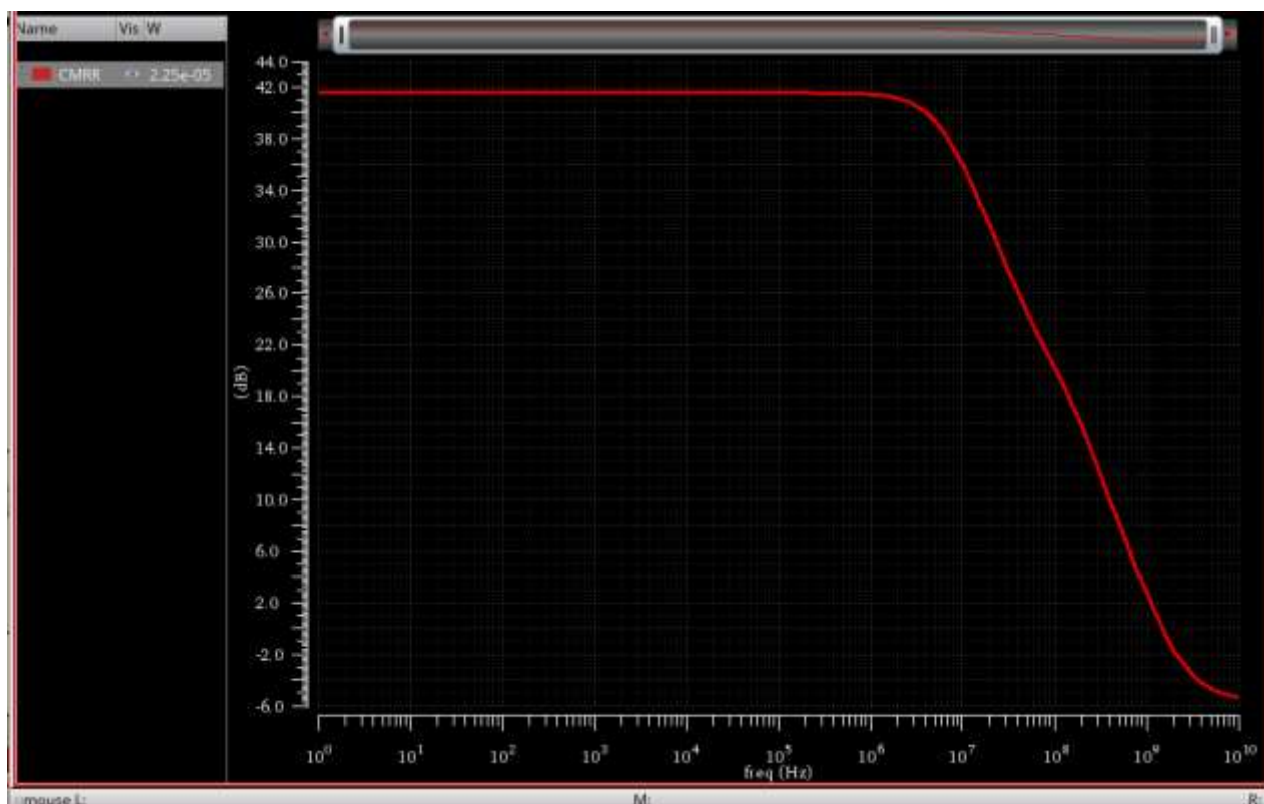
Q5

✚ Justify the variation of A_{vcm} vs frequency.

- A_{vCM} is Decreasing with Frequency as the Capacitor act as Open Circuit at low Frequencies, and Short Circuit at High Frequencies (Shunt) to ground.

Plot A_{vd}/A_{vcm} in dB. Compare A_{vd}/A_{vcm} @ DC with Hand Analysis in A Table.

Q6



P.O.C	Simulation	Hand Analysis
CMRR	41.92 dB	$CMRR = \left(\frac{A_{vd}}{A_{CM}} \right) = 1 + 2g_m R_{ss} = 42.38 \text{ dB}$

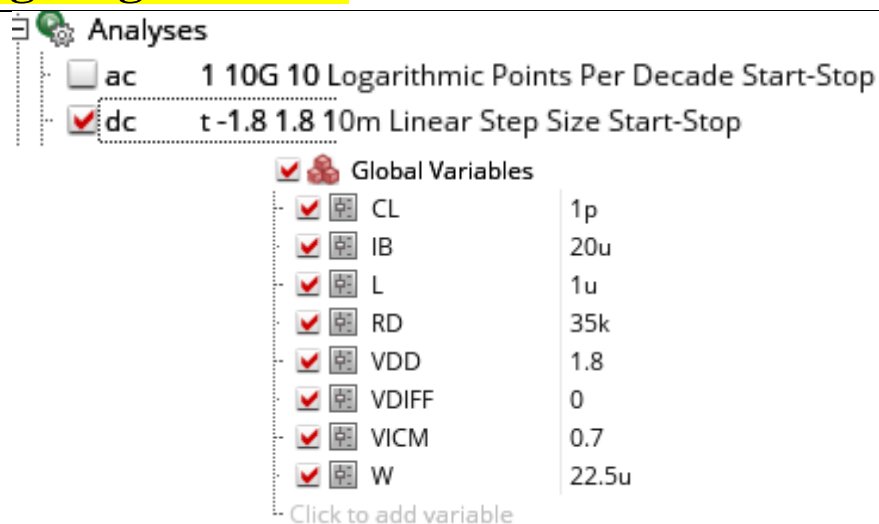
Q7

Justify the variation of A_{vd}/A_{vcm} with frequency.

- It is Nearly Constant at Low Frequencies while when Frequency Increases it will Decrease then the Pole make it decrease by a Slope = -20 dB/Decade . Parasitic capacitors which are in parallel with R_{ss} begins to contribute with lower impedance, so R_{ss} is getting lower at high frequencies.

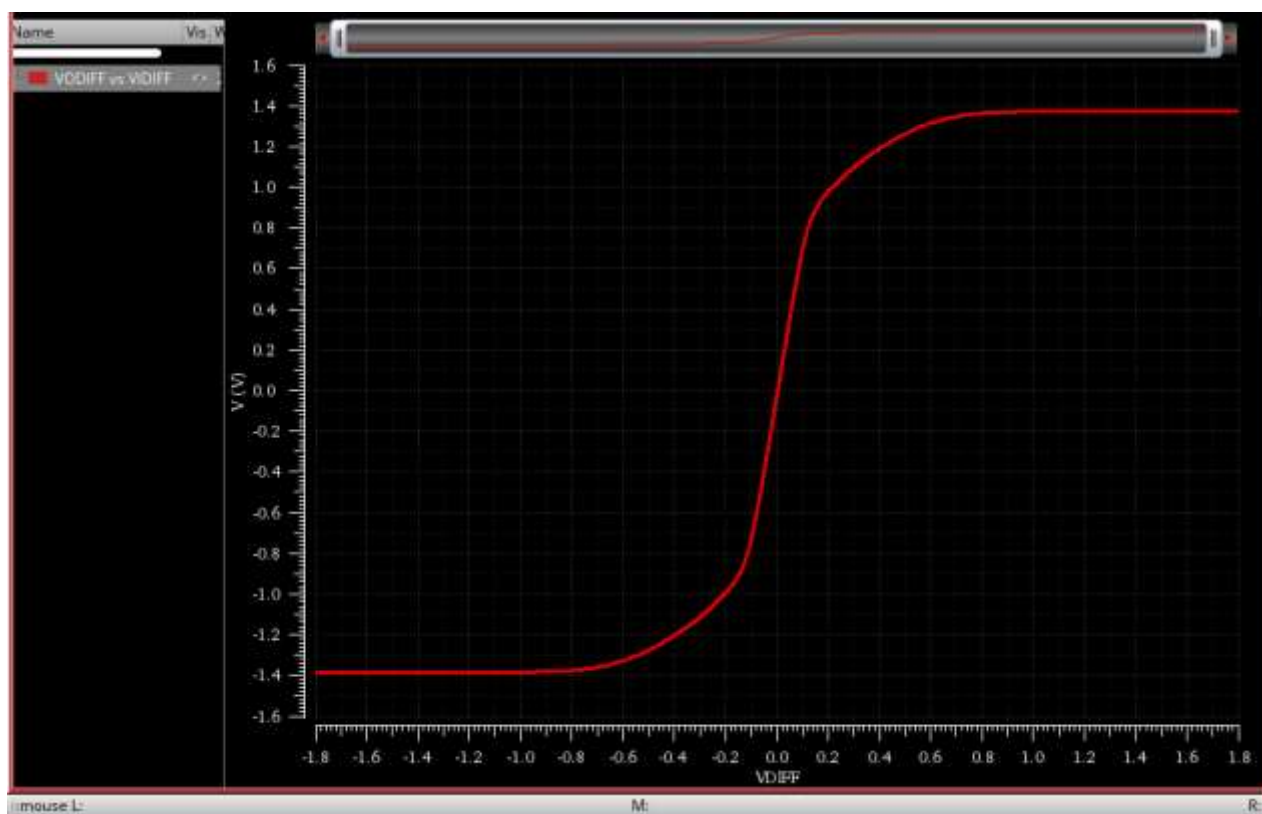
(4) Diff. Large Signal CCS.

Q1



Report diff large signal ccs (VODIFF vs VIDIFF).

Q2



✚ Compare the extreme values with hand analysis in a table.

○ Full Switching Occur (All Current Flows in M_1):

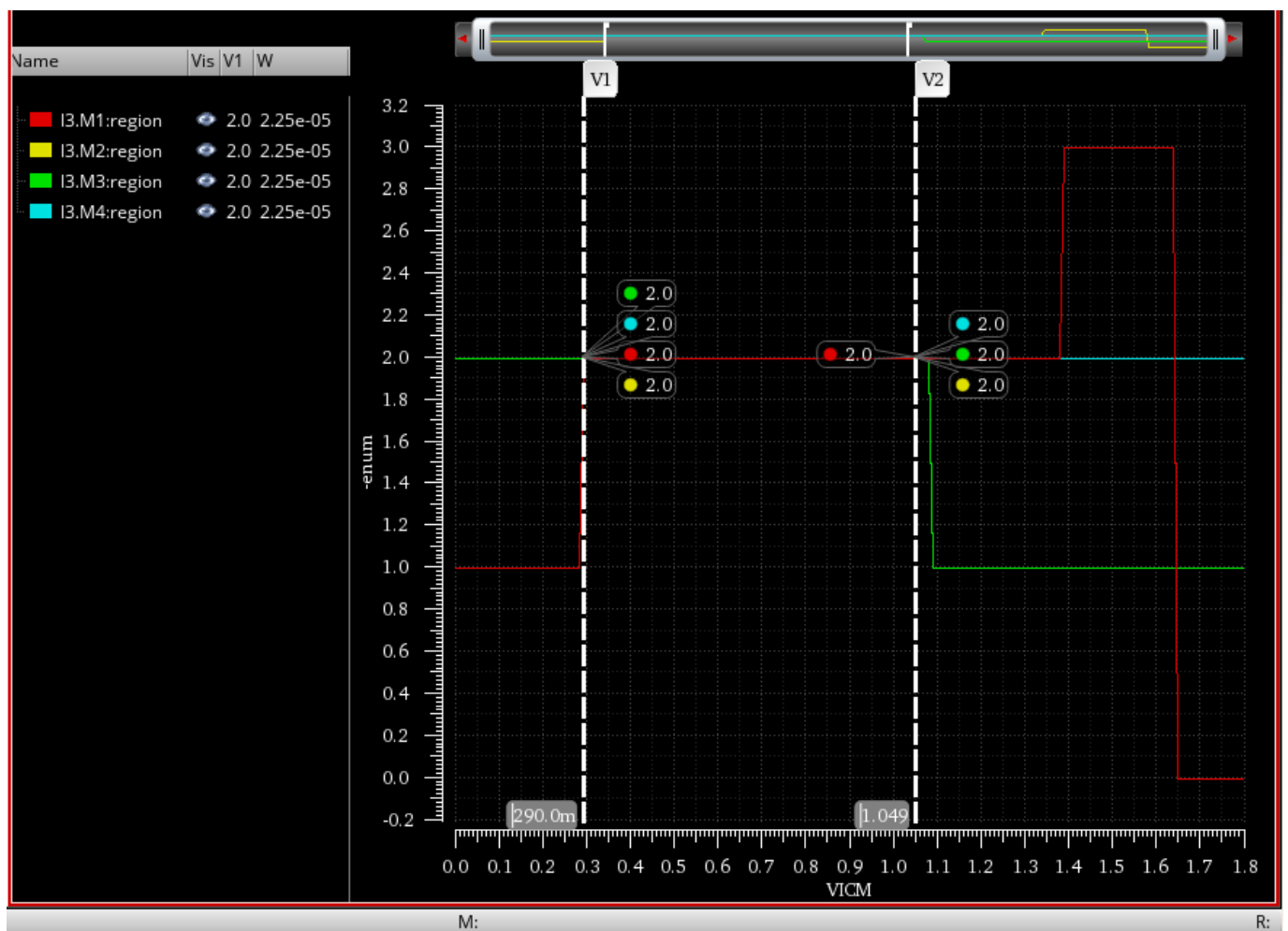
$$I_d = I_{SS} = 40 \mu A, V_{out} = I_d R_d = 40 \mu * 35k = 1.4 V.$$

P.O.C	Simulation	Hand Analysis
V_{out} Diff.	1.3792 V	1.4 V

(5) CM Large Signal CCS. (Region vs VICM)

Plot “region” OP parameter vs VICM for the input pair and the tail current source.

Region	Meaning
0	Cut – off
1	Triode
2	Saturation
3	Sub – Threshold
4	Breakdown



✚ Find the CM input range (CMIR).

Compare with hand analysis.

→ To Make M_1 & M_2 In Saturation

$$V_g = V_{ICM} > V_D - |V_{th}|, R_D = \frac{V_{outCM}}{I_D} = \frac{0.7 \text{ V}}{20 \mu\text{A}} = 35 \text{ k}\Omega$$

Since, $V_D = 0.7 \text{ V}$, $V_{th} = 0.41 \text{ V}$.

$$V_{ICM} \geq -|V_{th}| + \frac{1}{2} I_{SS} R_D$$

$$V_{ICM_{Min}} = V_D - V_{th} = 0.29 \text{ V} \quad (1).$$

→ To Make M_3 In Saturation

$$V_{DD} = V_{ov3} + V_{sg1} + V_{ICM_{Max}}$$

$$V_{ICM_{Max}} = V_{DD} - V_{ov3} - (V_{ov1} + |V_{th}|)$$

$$\text{Since, } V_{ov3} = V_{ov1} = 170.5 \text{ mV.}, V_{th} = 0.41 \text{ V} \quad (2).$$

$$V_{ICM_{Max}} = V_{DD} - 2V_{ov} - |V_{th}| = 1.049 \text{ V}.$$

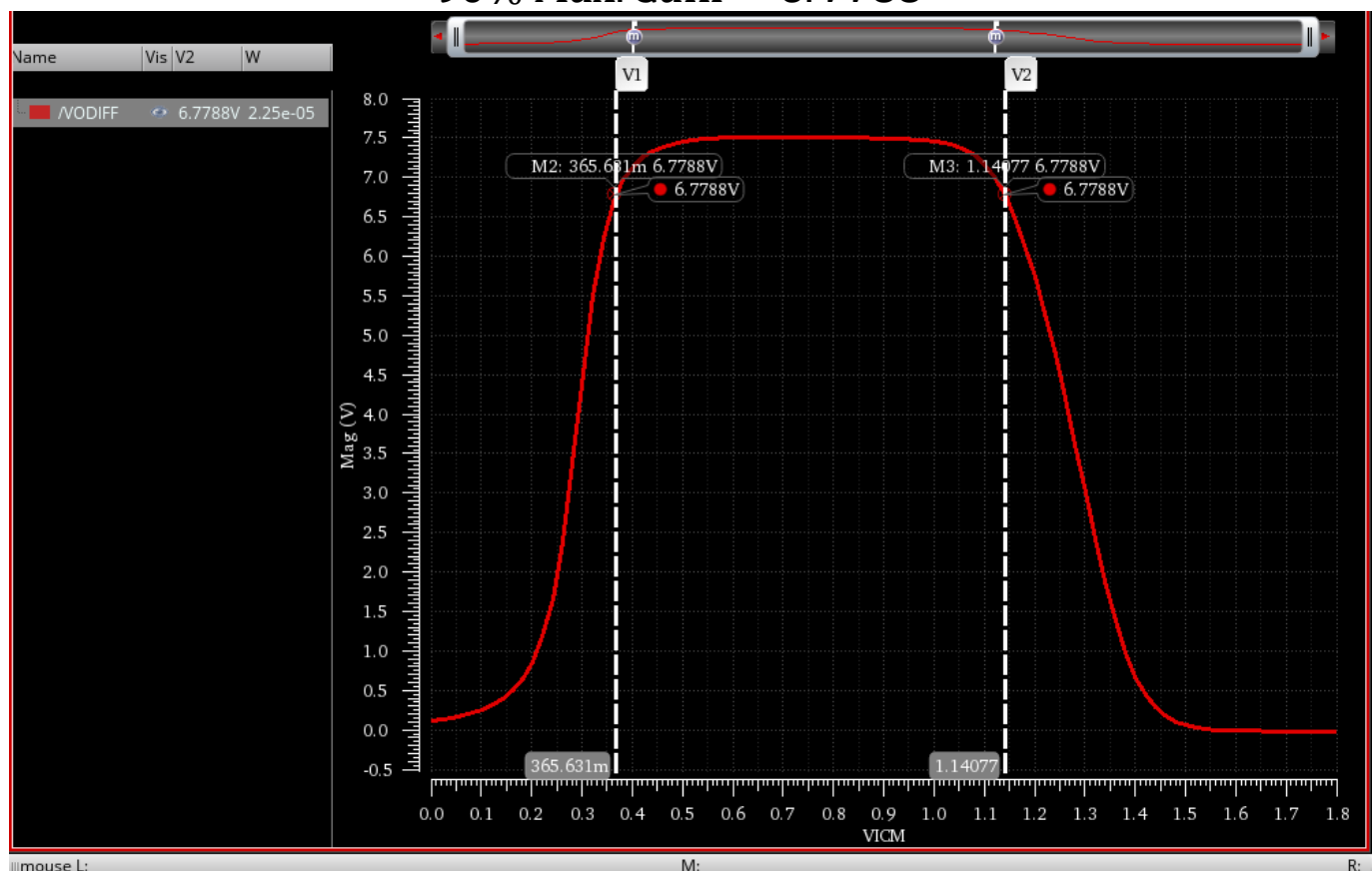
○ As Shown in Figure above in the CMIR all Transistors is in Sat.

(6) CM Large Signal CCS. (GBW vs VICM)

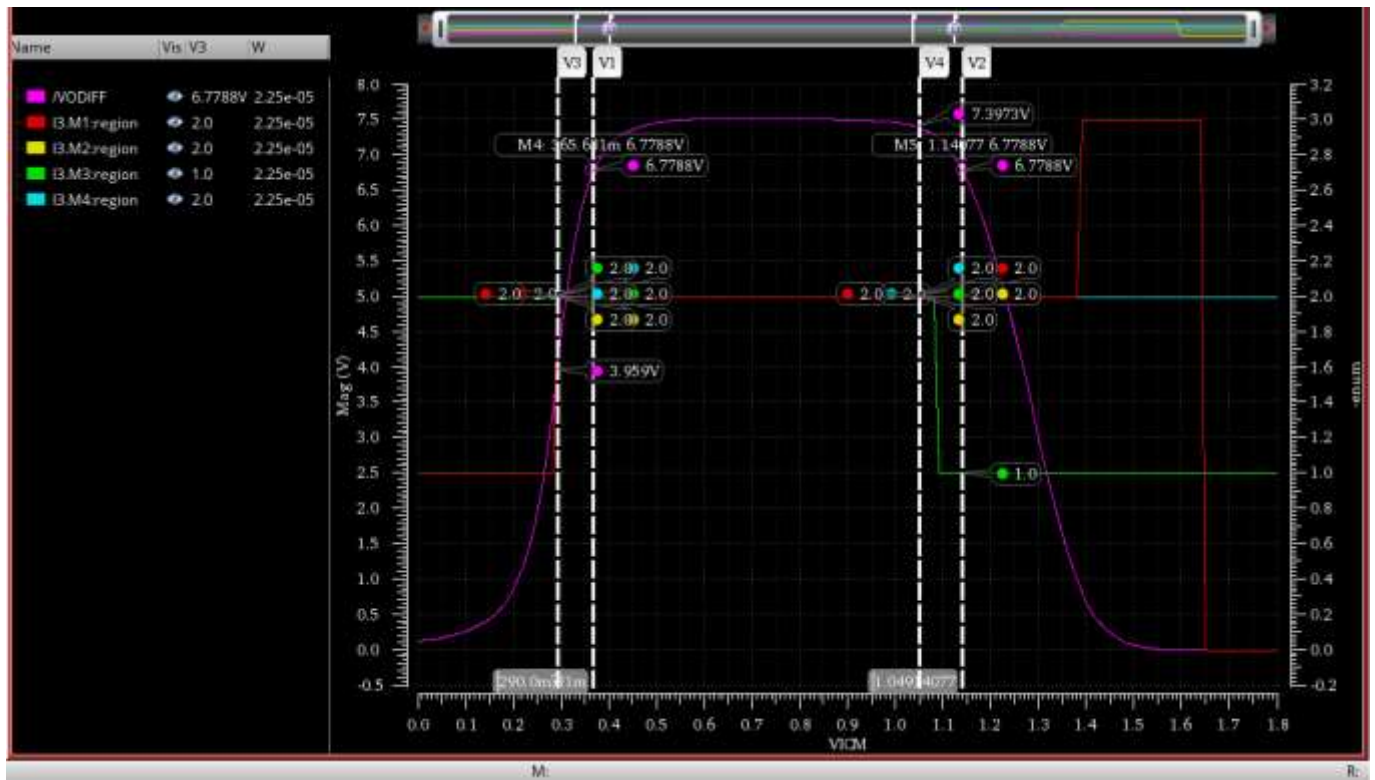
IEEE_Workshop:lab_06_diff_amp_tb:1	Diff Gain Large	
IEEE_Workshop:lab_06_diff_amp_tb:1	max gain	7.532

Max. Gain = 7.532

90% Max. Gain = 6.7788



Plot the results overlaid on the results of the previous method (region parameter).



Find the CM input range. Compare with the previous method in a table.

From the Graphs Above.

VICM	Regions	90% A_{vd}
Minimum	0.29 V.	0.365 V.
Maximum	1.049 V.	1.14 V.